PNP/NPN Epitaxial Planar Silicon Transistors



2SB1143/2SD1683

50V/4A Switching Applications

Applications

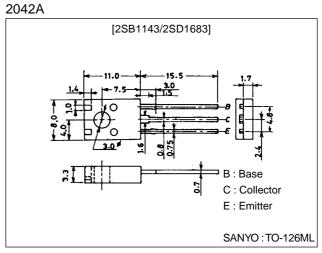
· Voltage regulators, relay drivers, lamp drivers, electrical equipment.

Features

- · Adoption of FBET, MBIT processes.
- · Low saturation voltage.
- · Large current capacity and wide ASO.

Package Dimensions

unit:mm



():2SB1143

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(–)60	V
Collector-to-Emitter Voltage	VCEO		(–)50	V
Emitter-to-Base Voltage	VEBO		()6	V
Collector Current	ι _C		()4	A
Collector Current (Pulse)	ICP		(–)6	A
Collector Dissipation	PC		1.5	W
		Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)40V, I _E =0			(–)1	μA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)1	μA
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)100mA	100*		560*	
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)3A	40			
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)50mA		150		MHz
Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(39)25		pF

 \ast ; The 2SB1143/2SD1683 are classified by 100mA h_{FE} as follows :

100 R 200 140 S 280 200 T 400 28	280 U 560
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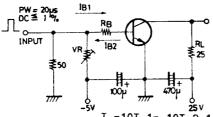
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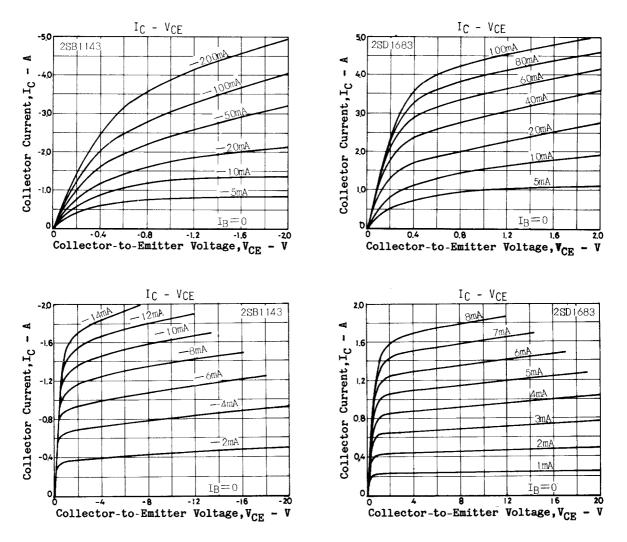
2SB1143/2SD1683

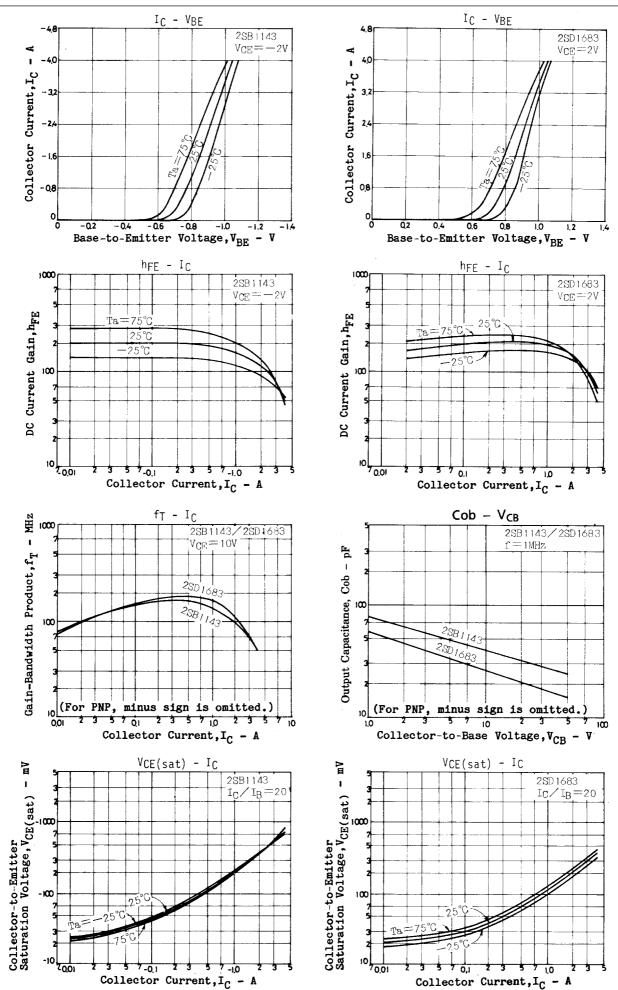
Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)2A, I _B =(-)100mA		(–350)	(700)	mV
				190	500	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)2A, I _B =(-)100mA		(–)0.94	(–)1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10μΑ, I _E =0	(–)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(–)50			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μA, I _C =0	(–)6			V
Turn-ON Time	ton	See specified Test Circuit		(70)70		ns
Storage Time	tstg	See specified Test Circuit		(450)		ns
				650		ns
Fall Time	t _f	See specified Test Circuit		(30)35		ns

Switching Time Test Circuit

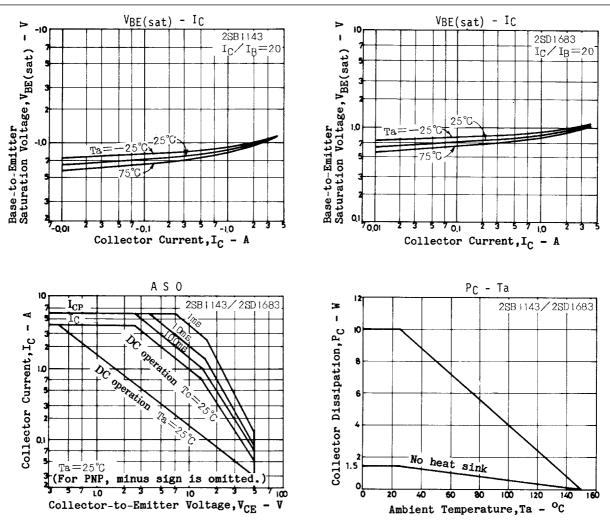


 $I_C = 10I_B 1 = -10I_B 2 = 1A$ (For PNP, the polarity is reversed.) Unit (resistance : Ω , capacitance : F)





2SB1143/2SD1683



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